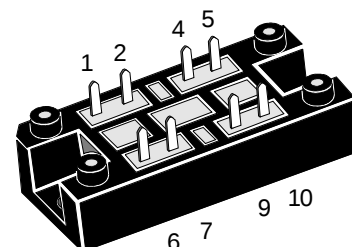
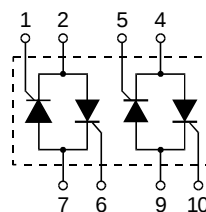


AC Controller Modules

$$I_{RMS} = 2 \times 30 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	VW2x30-08io1
1200	1200	VW2x30-12io1
1400	1400	VW2x30-14io1
1600	1600	VW2x30-16io1



Symbol	Test Conditions		Maximum Ratings	
I_{RMS}	$T_C = 85^{\circ}C$, (per phase)		30	A
I_{TRMS}	$T_{VJ} = T_{VJM}$		22	A
I_{TAVM}	$T_C = 85^{\circ}C$; (180° sine ; per thyristor)		14	A
I_{TSM}	$T_{VJ} = 45^{\circ}C$;	$t = 10\text{ ms}$ (50 Hz), sine	200	A
	$V_R = 0$	$t = 8.3\text{ ms}$ (60 Hz), sine	210	A
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$ (50 Hz), sine	180	A
	$V_R = 0$	$t = 8.3\text{ ms}$ (60 Hz), sine	190	A
I^2t	$T_{VJ} = 45^{\circ}C$	$t = 10\text{ ms}$ (50 Hz), sine	200	A ² s
	$V_R = 0$	$t = 8.3\text{ ms}$ (60 Hz), sine	190	A ² s
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$ (50 Hz), sine	160	A ² s
	$V_R = 0$	$t = 8.3\text{ ms}$ (60 Hz), sine	150	A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $f = 50\text{ Hz}$, $t_p = 200\text{ }\mu s$ $V_D = 2/3\text{ }V_{DRM}$ $I_G = 0.45\text{ A}$ $di_G/dt = 0.45\text{ A}/\mu s$	repetitive, $I_T = 45\text{ A}$	100	A/ μs
		non repetitive, $I_T = I_{TAVM}$	500	A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3\text{ }V_{DRM}$	1000	V/ μs
P_{GM}	$T_{VJ} = T_{VJM}$	$t_p = 30\text{ }\mu s$	10	W
	$I_T = I_{TAVM}$	$t_p = 300\text{ }\mu s$	5	W
P_{GAVM}			0.5	W
V_{RGM}			10	V
T_{VJ}			-40...+125	°C
T_{VJM}			125	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	$t = 1\text{ min}$	3000	V~
	$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$	3600	V~
M_d	Mounting torque (M5)		2-2.5/18-22 Nm/lb.in.	
Weight	typ.		35	g

Features

- Thyristor controller for AC (circuit W2C acc. to IEC) for mains frequency
- Soldering connections for PCB mounting
- Isolation voltage 3600 V~
- Planar passivated chips
- UL applied

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 45$ A; $T_{VJ} = 25^\circ\text{C}$	≤ 1.81 V
V_{T0}	For power-loss calculations only	0.8 V
r_T		25 m Ω
V_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 1.5 V
	$T_{VJ} = -40^\circ\text{C}$	≤ 1.6 V
I_{GT}	$V_D = 6$ V; $T_{VJ} = 25^\circ\text{C}$	≤ 100 mA
	$T_{VJ} = -40^\circ\text{C}$	≤ 200 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}		≤ 5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10$ μs $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 450 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6$ V; $R_{GK} = \infty$	≤ 200 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45$ A; $di_G/dt = 0.45$ A/ μs	≤ 2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20$ A, $t_p = 200$ μs ; $di/dt = -10$ A/ μs $V_R = 100$ V; $dv/dt = 15$ V/ μs ; $V_D = 2/3 V_{DRM}$	typ. 150 μs
R_{thJC}	per thyristor; DC	1.7 K/W
	per module	0.43 K/W
R_{thJK}	per thyristor; DC	2.0 K/W
	per module	0.5 K/W
d_s	Creeping distance on surface	12.7 mm
d_A	Creepage distance in air	9.4 mm
a	Max. allowable acceleration	50 m/s ²

Dimensions in mm (1 mm = 0.0394")

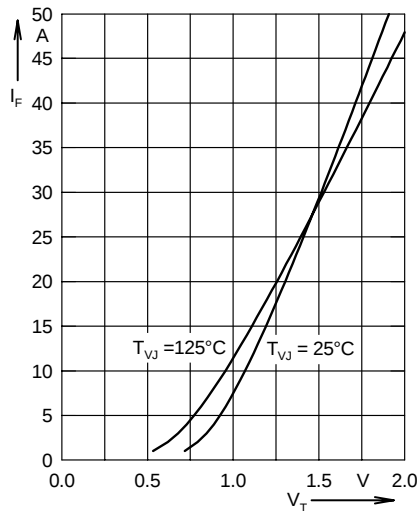
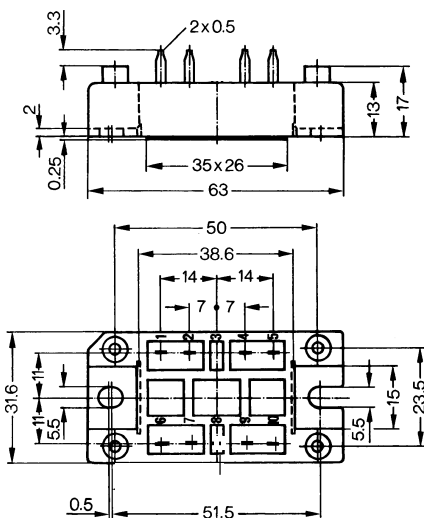


Fig. 3 Forward current versus voltage drop per leg

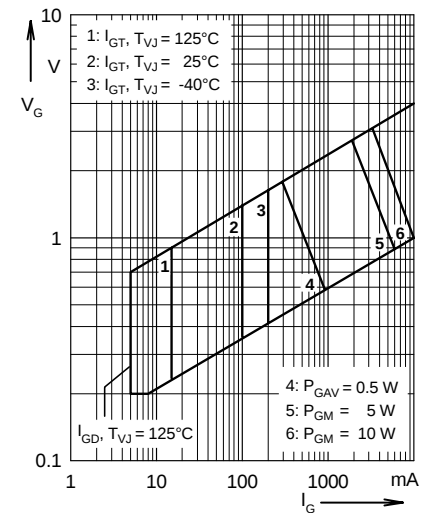


Fig. 1 Gate trigger characteristics

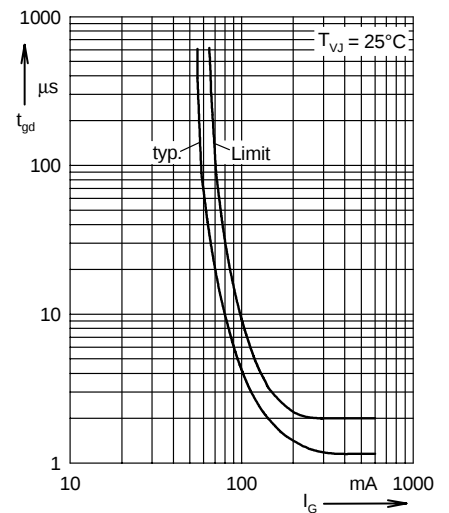


Fig. 2 Gate trigger delay time

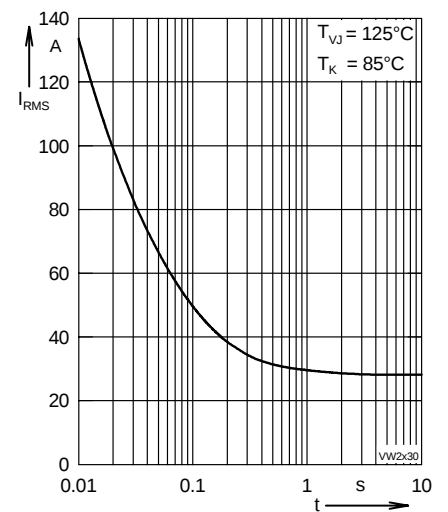


Fig. 4 Rated RMS current versus time (360° conduction)

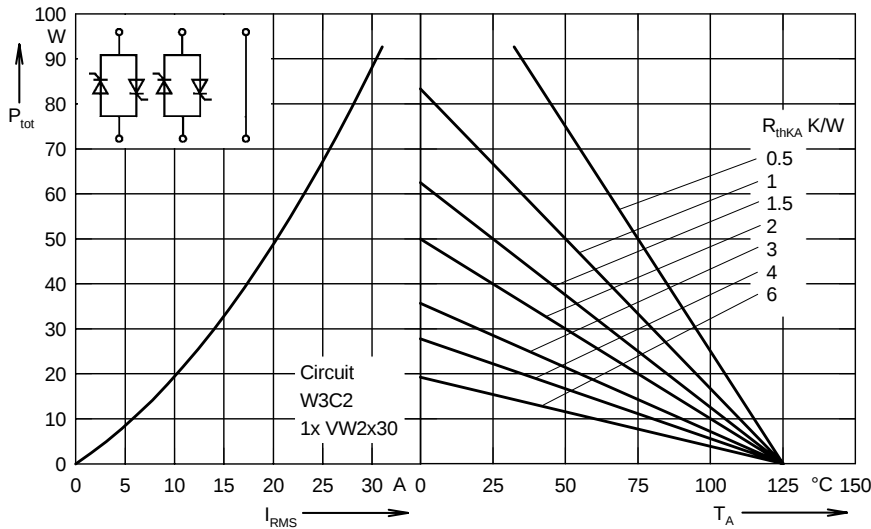


Fig. 5 Load current capability for two phase AC controller

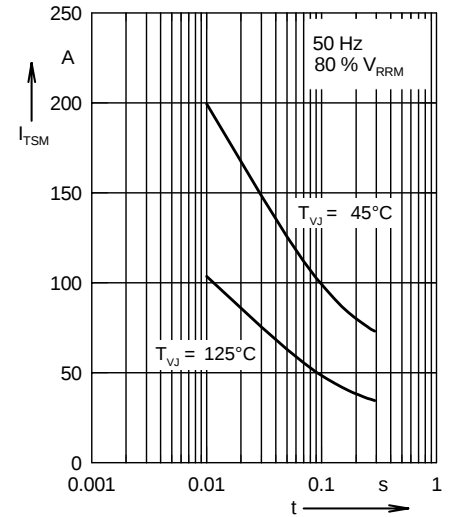


Fig. 6 Surge overload current

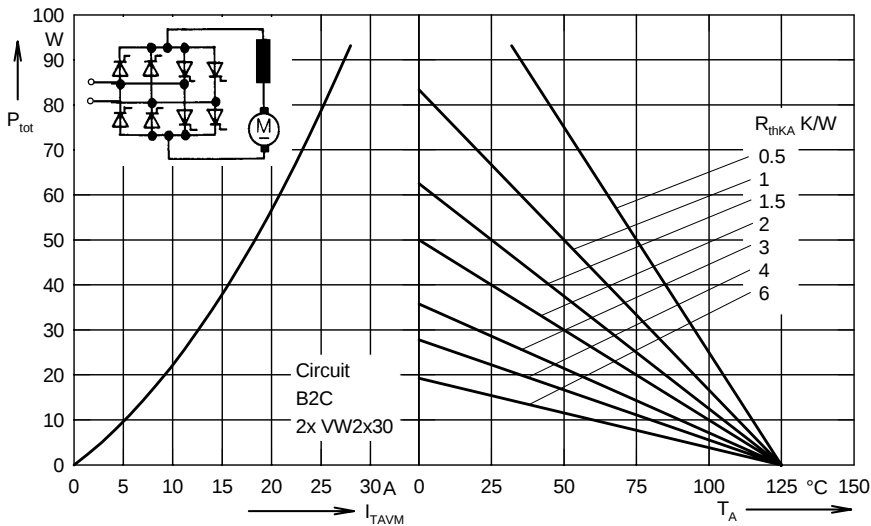


Fig. 7 Power dissipation versus direct output current and ambient temperature cyclo converter, four quadrant operation

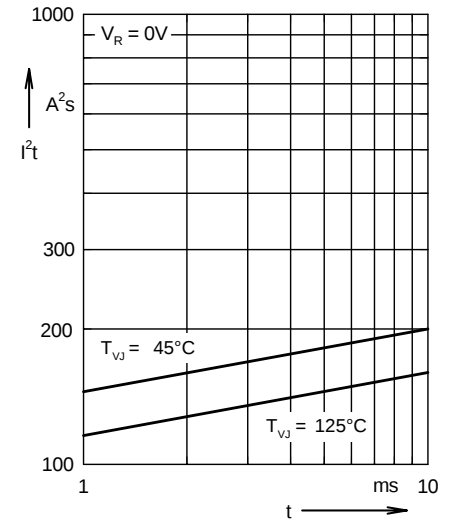


Fig. 8 I^2t versus time (per thyristor)

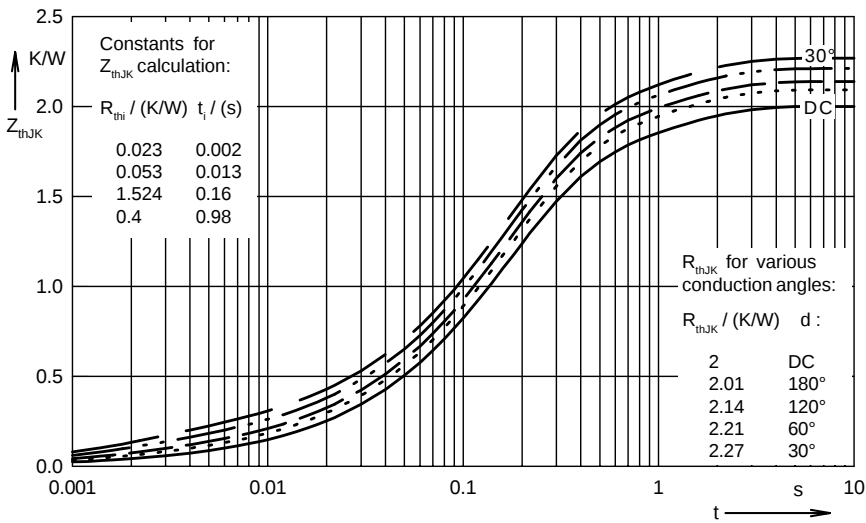


Fig. 9 Transient thermal impedance junction to heatsink (per thyristor)

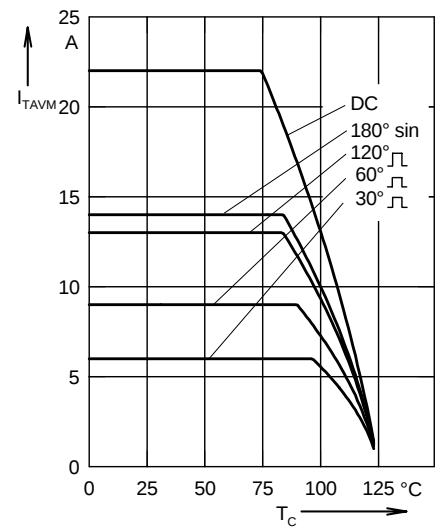


Fig. 10 Maximum forward current at case temperature